

性能特点：

- 频带：6~18GHz
- 插入损耗：0.6dB/0.6dB/1dB/1.1dB/1.1dB/1.1dB
- 均衡量：2dB/3dB/4dB/5dB/6dB/7dB
- 输入/输出电压驻波比：1.2/1.2
- 芯片尺寸：0.6mm×0.6mm×0.1mm

产品简介：

HH-AE0618-2、HH-AE0618-3、HH-AE0618-4、HH-AE0618-5、HH-AE0618-6、HH-AE0618-7 是频率范围覆盖 6GHz-18GHz 的 GaAs MMIC 系列均衡器芯片。在频率范围内插损为正斜率，均衡量分别为 2dB、3dB、4dB、5dB、6dB、7dB。

电参数：(T_A=25°C)

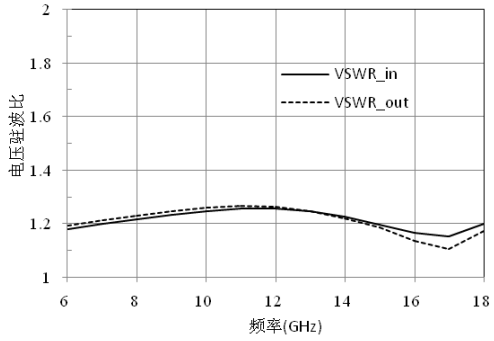
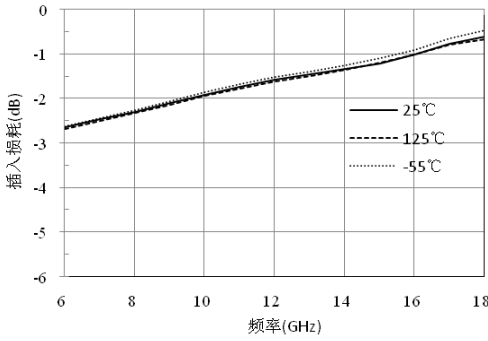
指标		最小值	典型值	最大值	单位
频率范围		6~18			GHz
插入损耗	HH-AE0618-2	0.6	-	2.6	dB
	HH-AE0618-3	0.6	-	3.5	dB
	HH-AE0618-4	1	-	5.0	dB
	HH-AE0618-5	1.1	-	5.9	dB
	HH-AE0618-6	1.1	-	7	dB
	HH-AE0618-7	1.1	-	8	dB
均衡量	HH-AE0618-2	-	2	-	dB
	HH-AE0618-3	-	3	-	dB
	HH-AE0618-4	-	4	-	dB
	HH-AE0618-5	-	5	-	dB
	HH-AE0618-6	-	6	-	dB
	HH-AE0618-7	-	7	-	dB
输入电压驻波比		-	1.2	1.3	-
输出电压驻波比		-	1.2	1.3	-

使用限制参数：(超过以上任何一项最大限额都有可能造成永久损坏。)

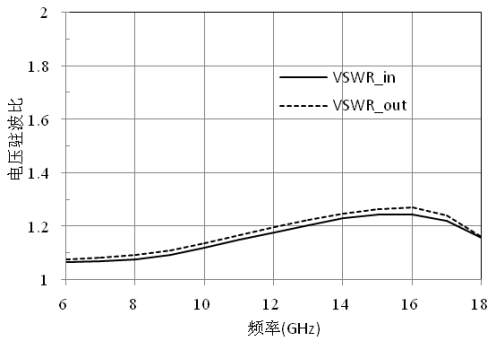
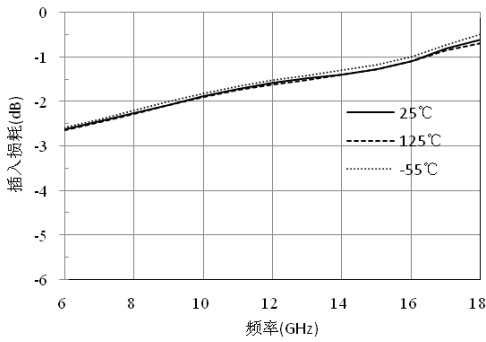
输入功率	+30dBm
存储温度	-65°C~150°C
使用温度	-55°C~125°C

典型曲线：

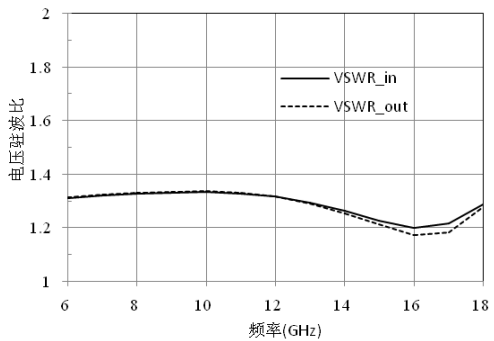
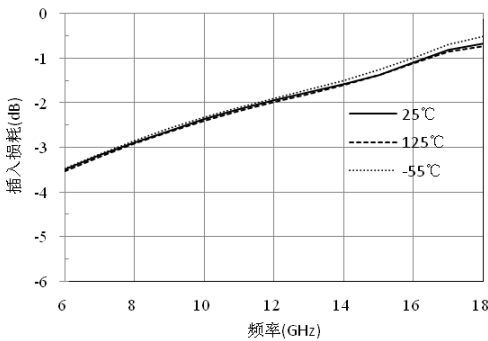
HH-AE0618-2 (on wafer)



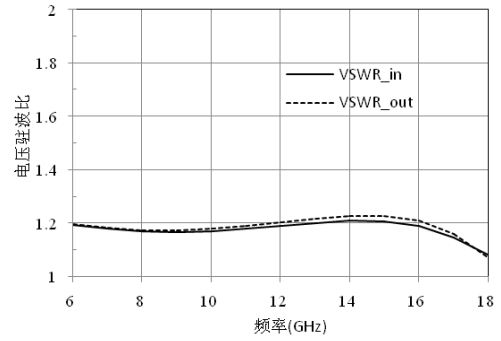
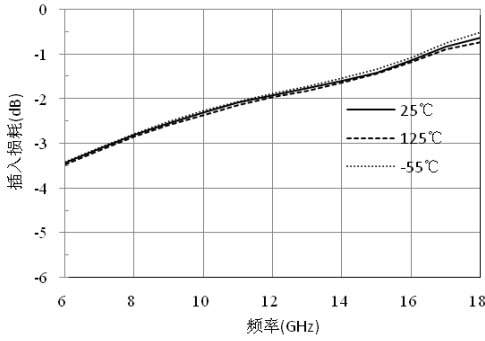
HH-AE0618-2 (bondwire)



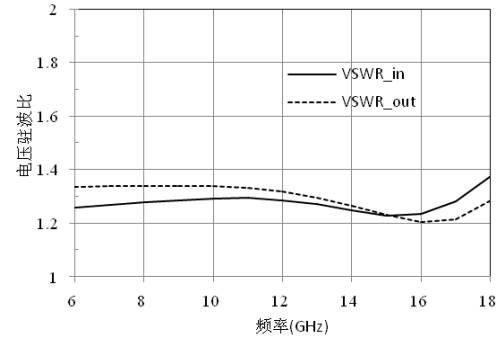
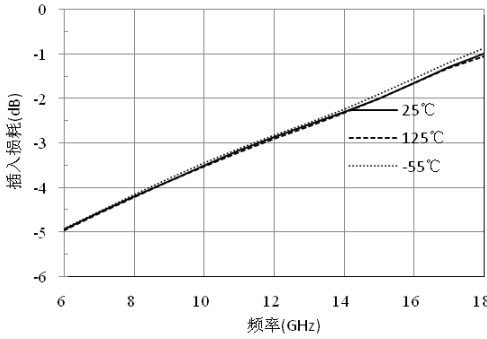
HH-AE0618-3 (on wafer)



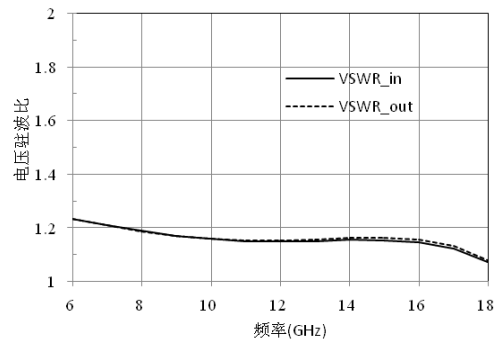
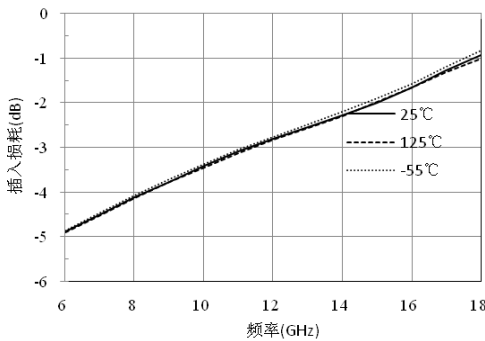
HH-AE0618-3 (bondwire)



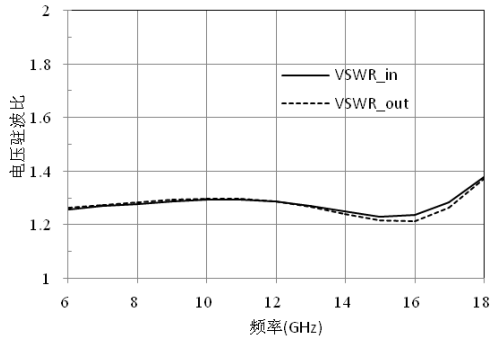
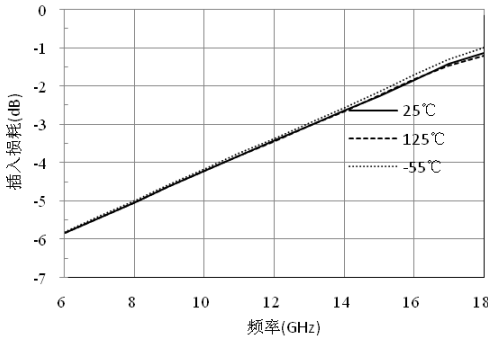
HH-AE0618-4 (on wafer)



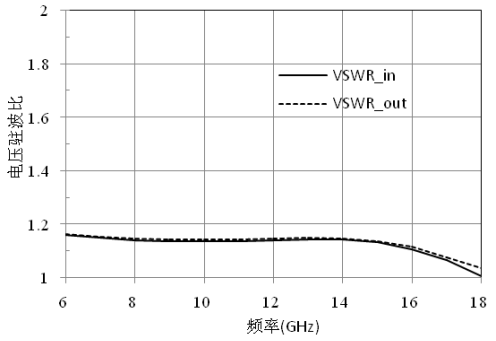
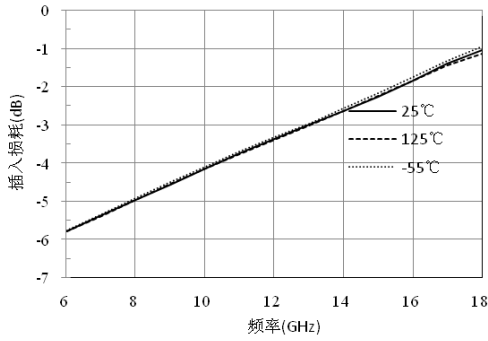
HH-AE0618-4 (bondwire)



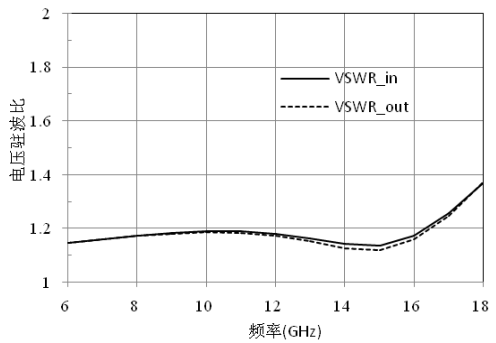
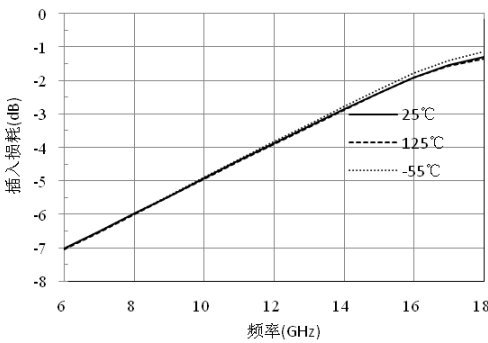
HH-AE0618-5 (on wafer)



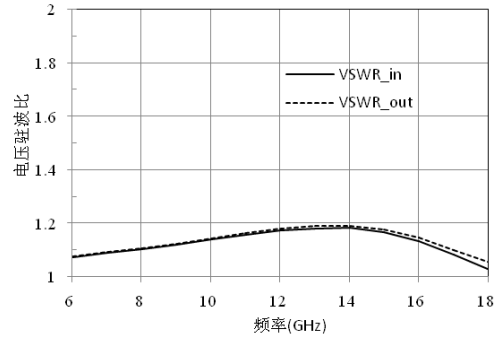
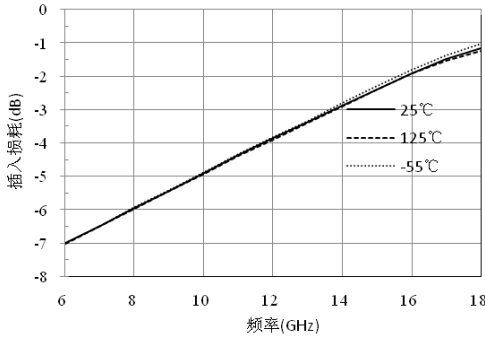
HH-AE0618-5 (bondwire)



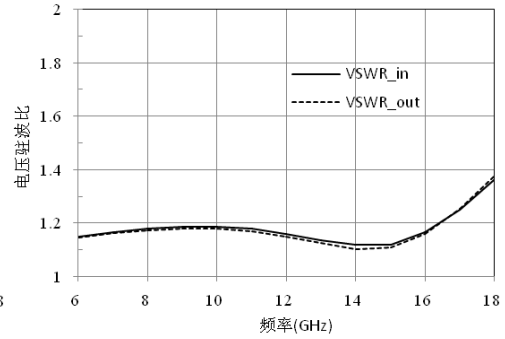
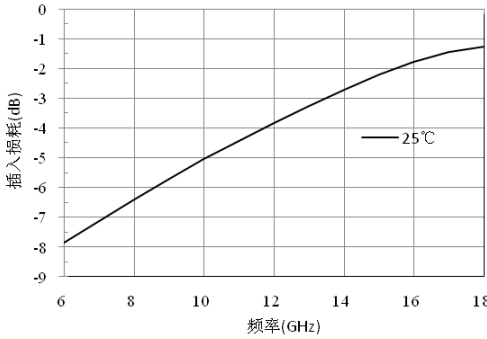
HH-AE0618-6 (on wafer)



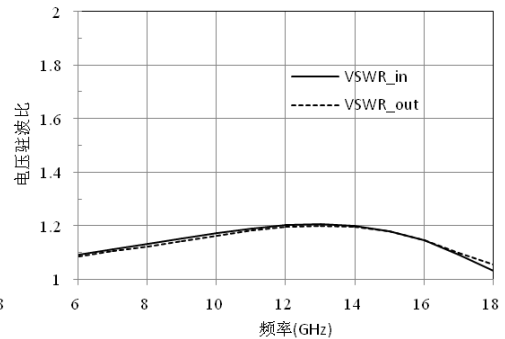
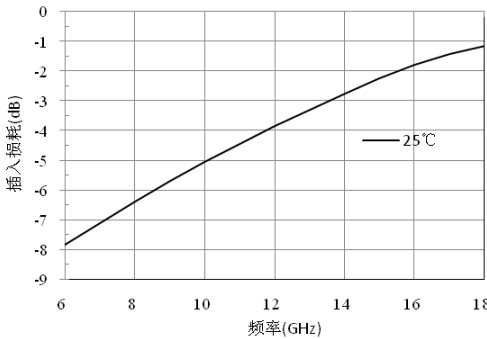
HH-AE0618-6 (bondwire)



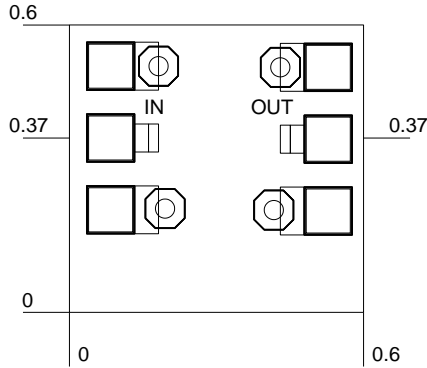
HH-AE0618-7 (on wafer)



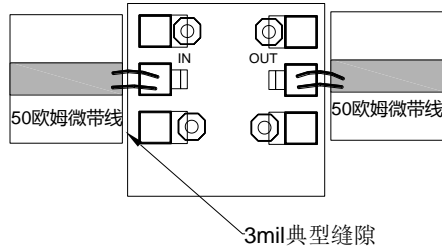
HH-AE0618-7 (bondwire)



尺寸图：(单位 mm)



建议装配图：



使用说明：

存储：芯片必须放置于具有静电防护功能的容器中，并在氮气环境下保存。

清洁处理：裸芯片必须在净化环境中操作使用，禁止采用液态清洁剂对芯片进行清洁处理。

静电防护：请严格遵守 ESD 防护要求，避免器件静电损伤。

常规操作：拿取芯片请使用真空夹头或精密尖头镊子。操作过程中要避免工具或手指触碰到芯片表面。

装架操作：芯片安装可采用 AuSn 焊料共晶焊接或导电胶粘接工艺。安装面必须清洁平整。

键合操作：输入输出各用 2 根 (建议直径 25um 金丝) 键合线，键合线长度小于 250um 最优。建议采用尽可能小的超声波能量。键合时起始于芯片上的压点，终止于封装 (或基板)。